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File: LDO_5V_3.kicad_sch

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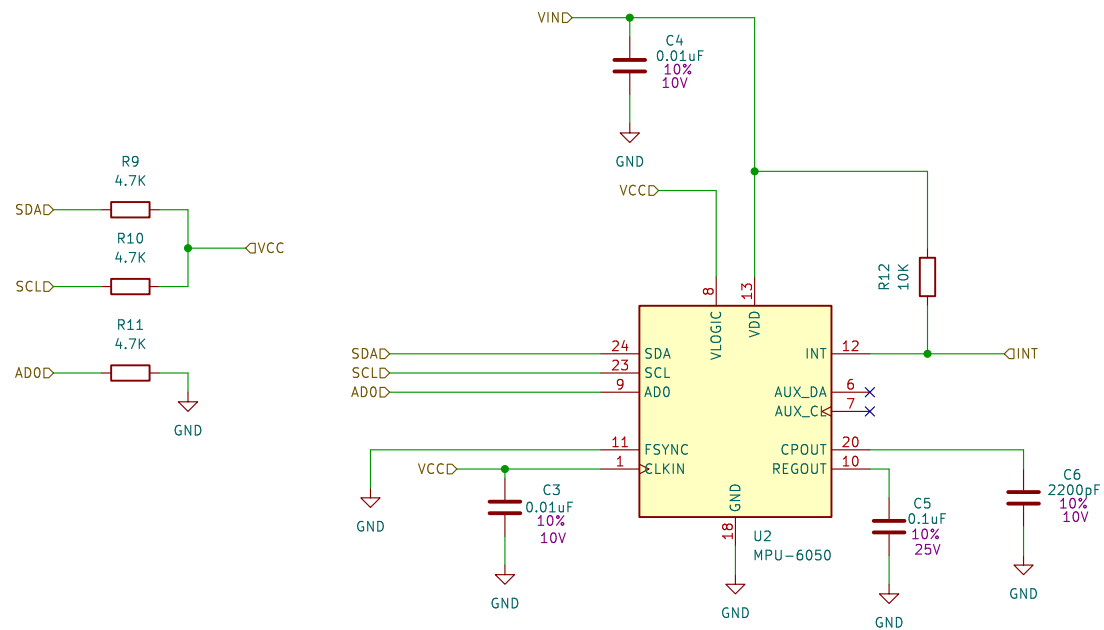
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Date:

KiCad E.D.A. kicad 7.0.8

Rev:

Id: 2/25



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File: imu_mpu6050.kicad_sch

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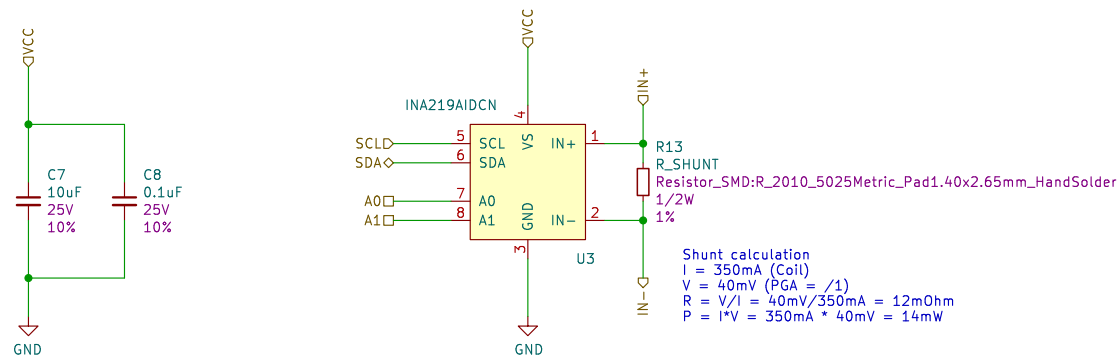
Size: A4

Date:

KiCad E.D.A. kicad 7.0.8

Rev:

Id: 3/25



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Sheet: /current_monitor/
 File: ina219.kicad_sch

Title:

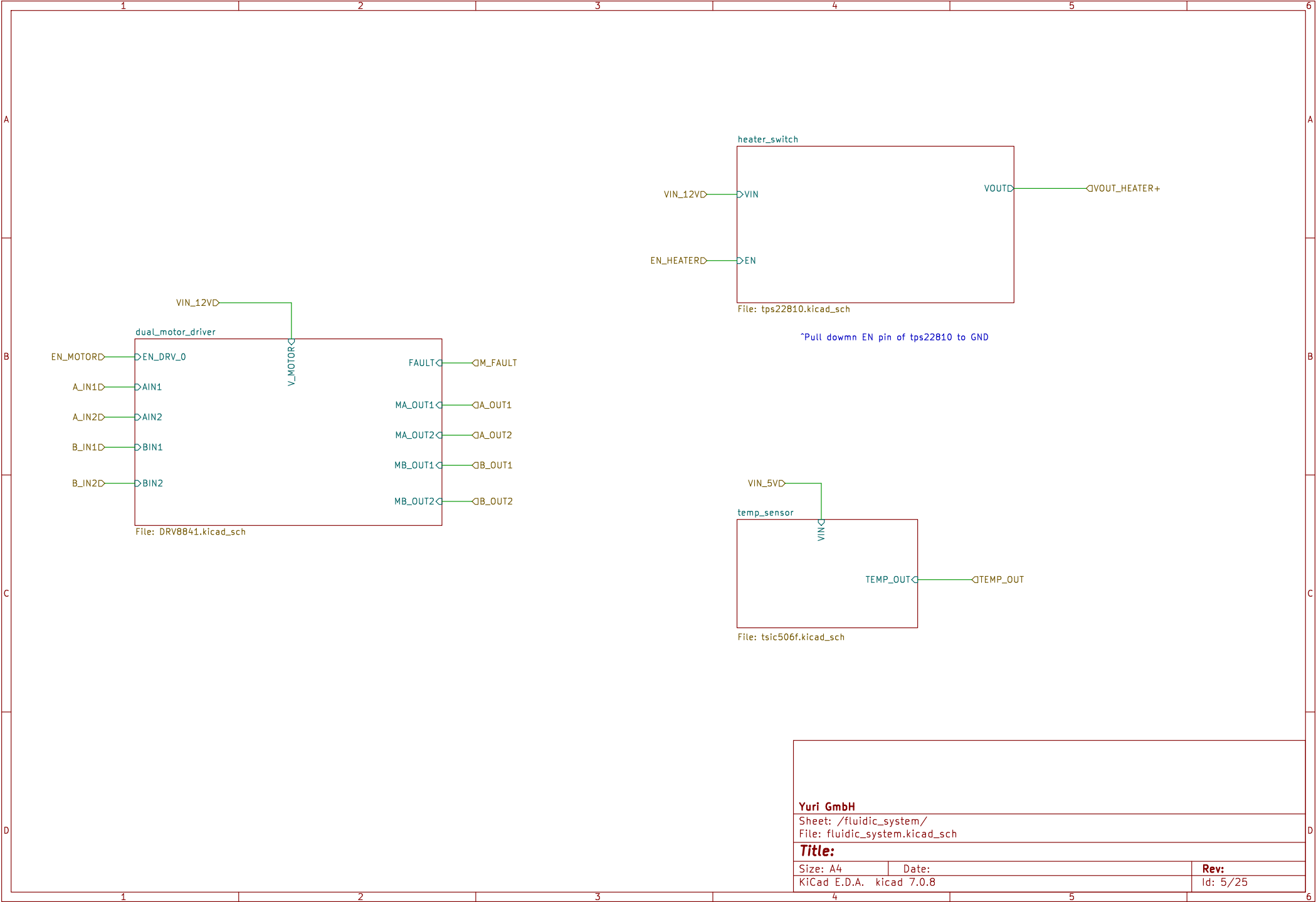
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Date:

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Rev:

Id: 4/25



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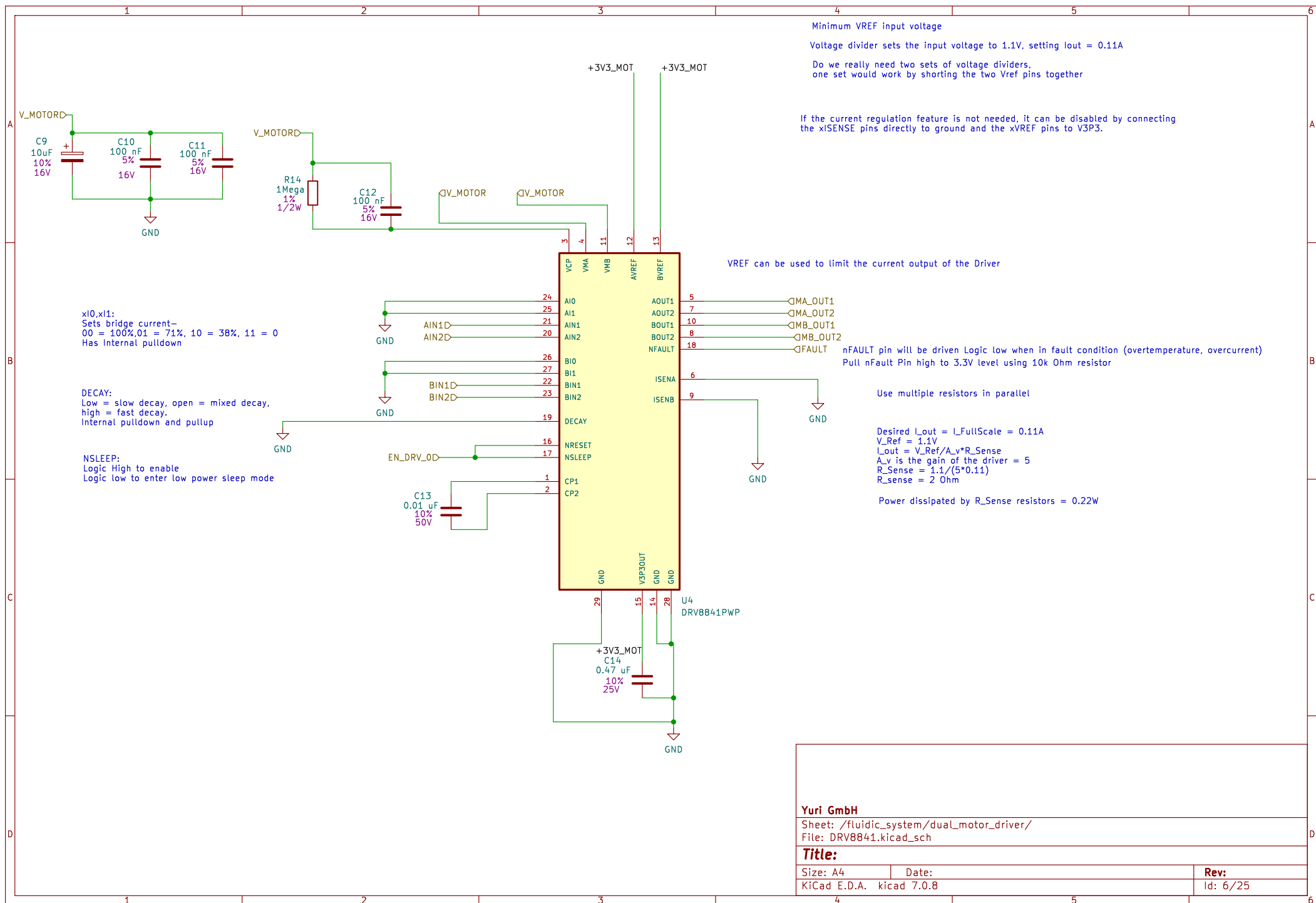
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File: fluidic_system.kicad_sch

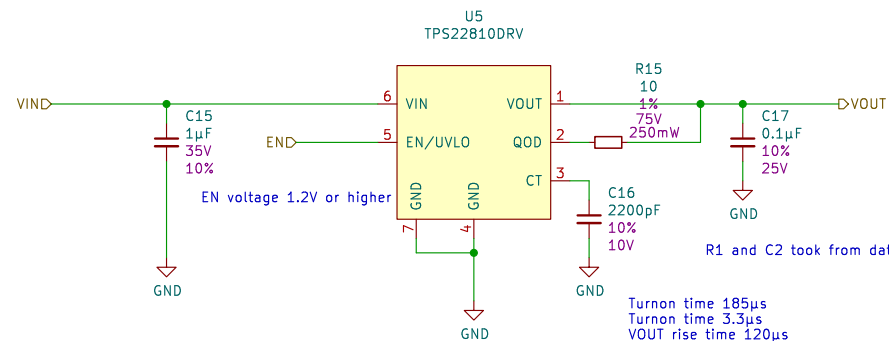
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Size: A4
KiCad E.D.A. kicad 7.0.8

Date:

Rev:
Id: 5/25





R1 and C2 took from datasheet §7.6 table as an example

Turnon time 185µs
Turnon time 3.3µs
VOUT rise time 120µs
VOUT fall time 2 µs
ON delay time 130 µs

C1 = 1µF should be 10 times bigger than output capacitor.
Othrwise it could cause the current flow through the body from VOUT to VIN.

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Sheet: /fluidic_system/heater_switch/
File: tps22810.kicad_sch

Title:

Size: A4

Date:

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Rev:

Id: 7/25

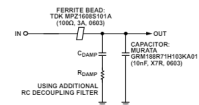
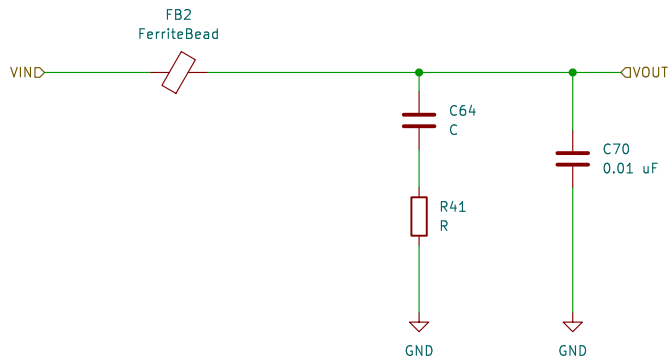


Figure 28. Additional RC Decoupling Filter

$$R_{DAMP} \geq 2 \sqrt{\frac{L_{BEAD}}{C_{DAMP}}} \quad (3)$$

$$R_{DAMP} \leq 0.5 \sqrt{\frac{L_{BEAD}}{C_{DECUP}}} \quad (4)$$

where:

R_{DAMP} is the damping resistance.

L_{BEAD} is the bead inductance from Equation 1, including external inductance such as the parasitic trace inductance of the board.

C_{DAMP} is the damping capacitance.

C_{DECUP} is the decoupling capacitance.

$$L_{BEAD} = \frac{X_L}{2 \times \pi \times f} \quad (1)$$

where:

f is the frequency point anywhere in the region the bead appears inductive. In this example, $f = 30.7$ MHz.

X_L is the reactance at 30.7 MHz, which is 233 Ω .

Equation 1 yields an inductance value (L_{BEAD}) of 1.208 μ H.

For the region where the bead appears most capacitive ($Z = |X_C|$; C_{DAMP}), the parasitic capacitance is calculated by the following equation:

$$C_{PAR} = \frac{1}{2 \times \pi \times f \times |X_C|} \quad (2)$$

where:

f is the frequency point anywhere in the region the bead appears capacitive. In this example, $f = 803$ MHz.

$|X_C|$ is the reactance at 803 MHz, which is 118.1 Ω .

Equation 2 yields a parasitic capacitance value (C_{DAMP}) of 1.678 pF.

Sheet: /EMI_FILTER1/
File: emi_filter_dc_dc.kicad_sch

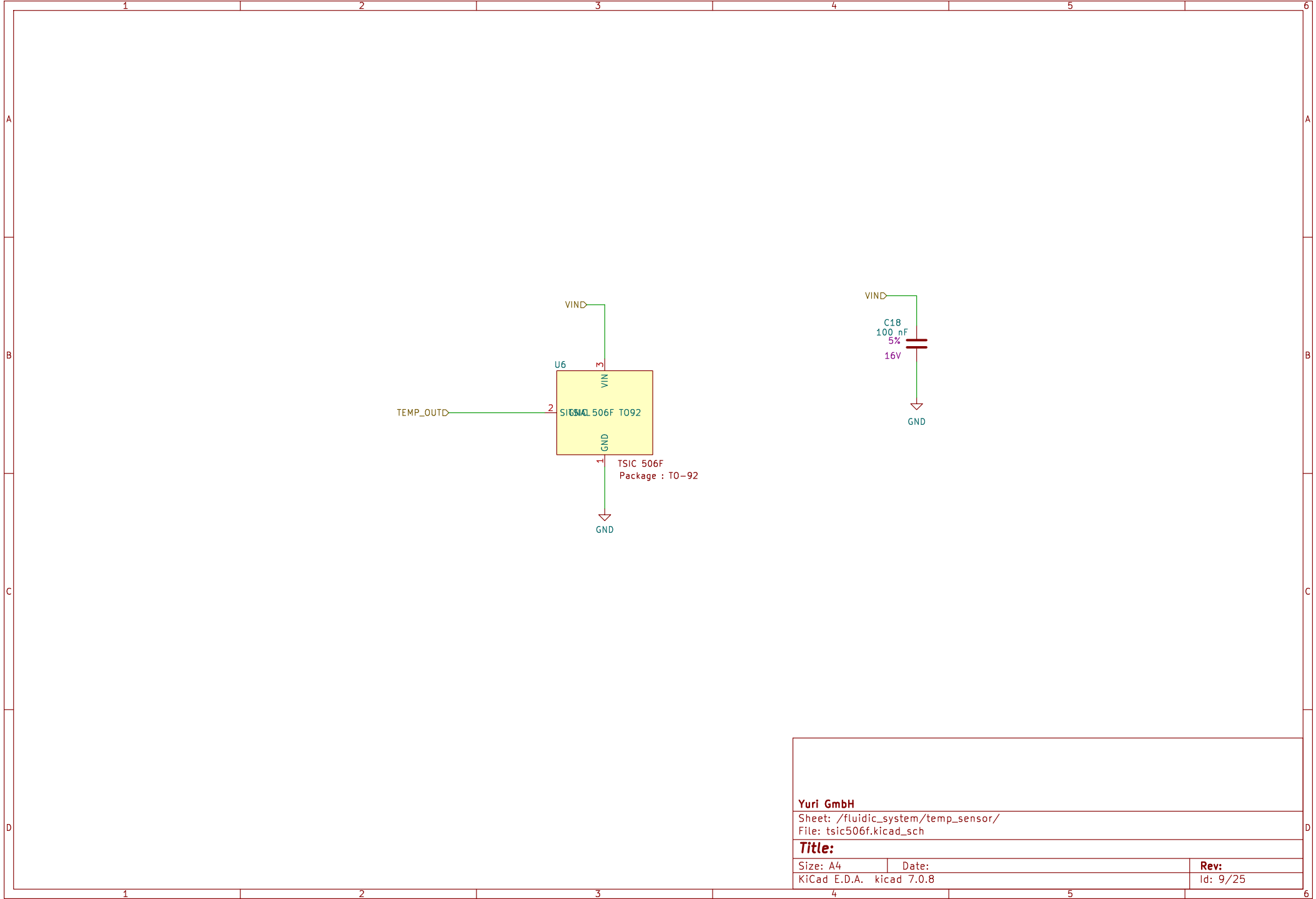
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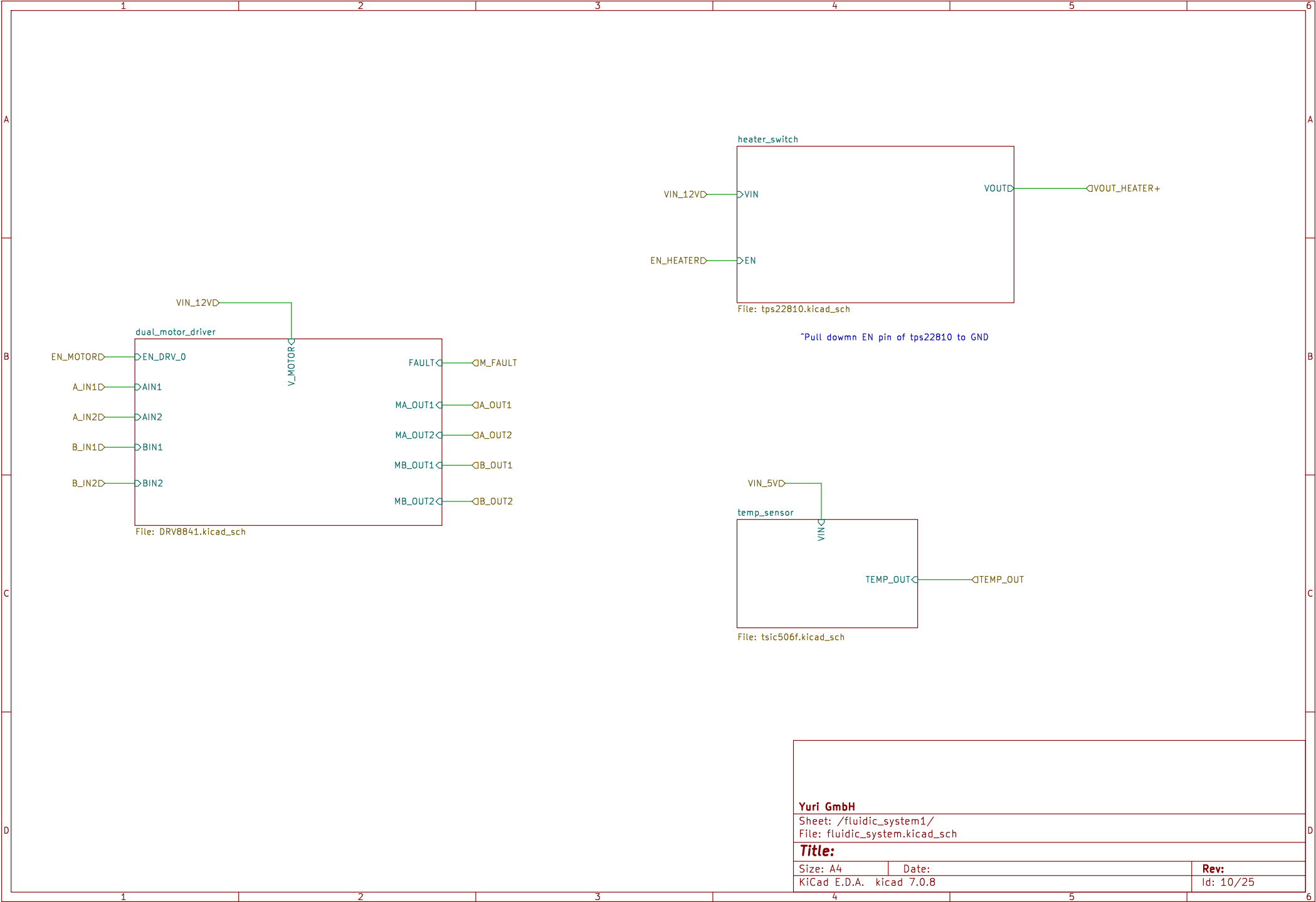
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KiCad E.D.A. kicad 7.0.8

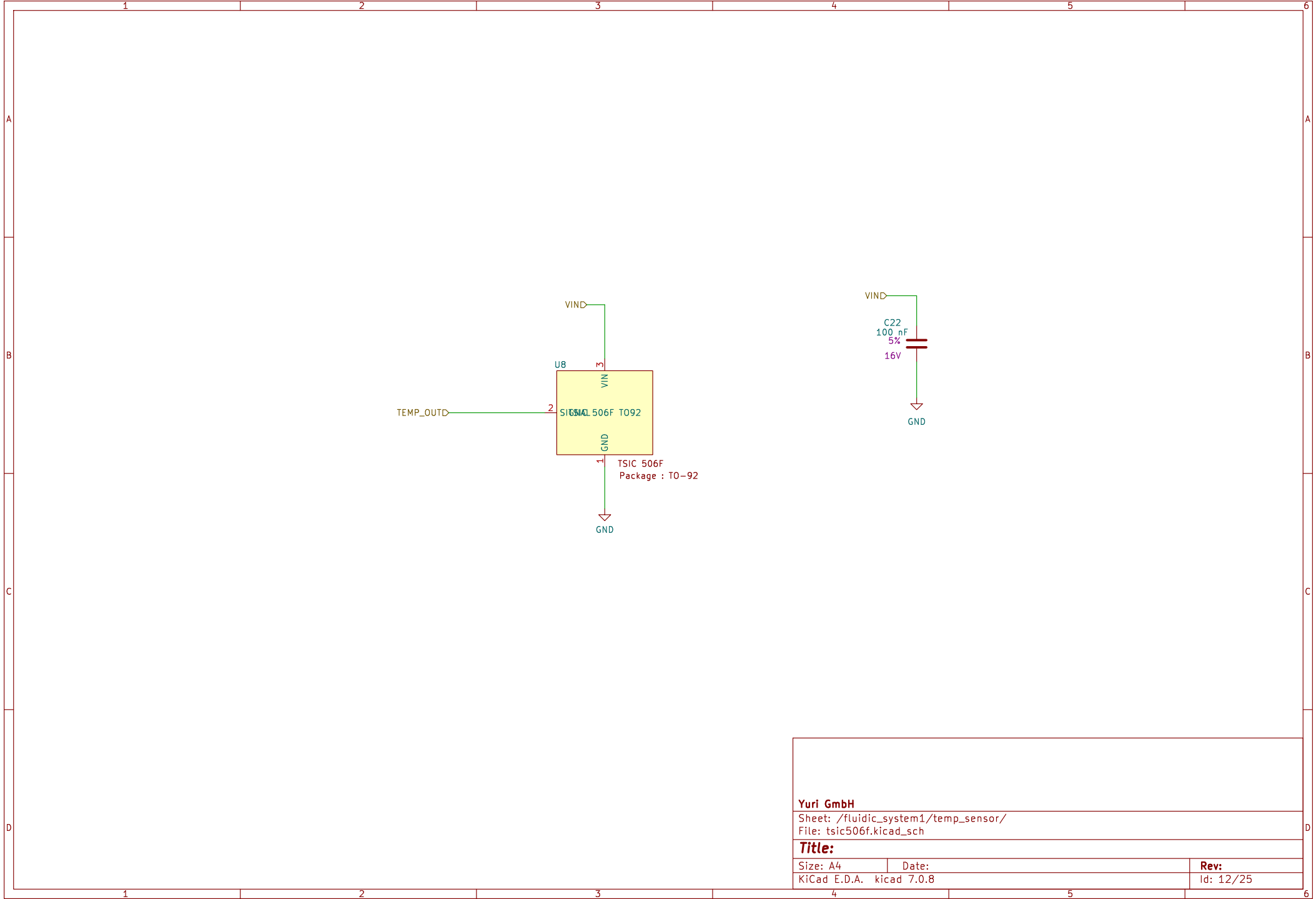
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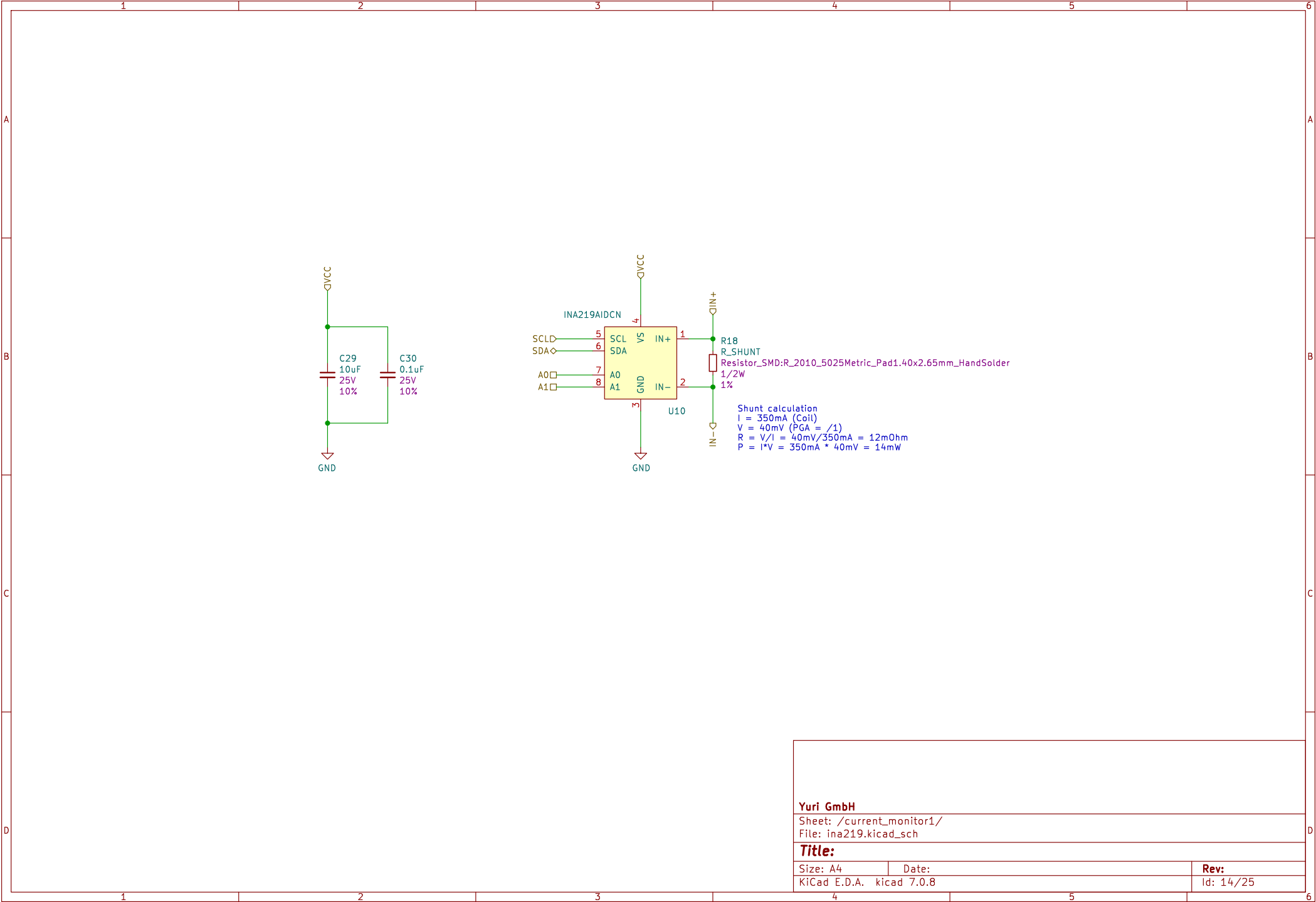
Rev:

Id: 8/25









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Sheet: /current_monitor1/
File: ina219.kicad_sch

Title:

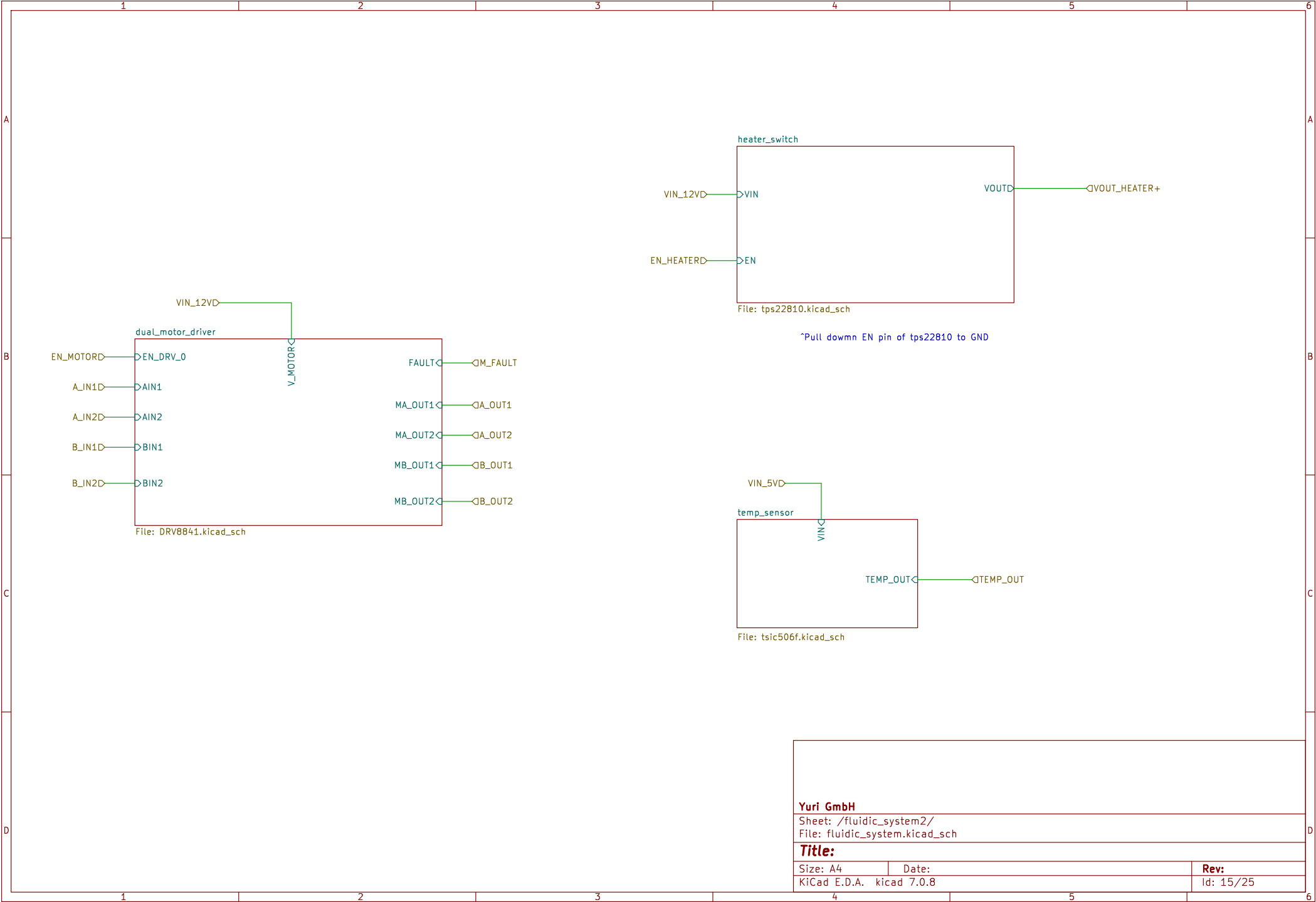
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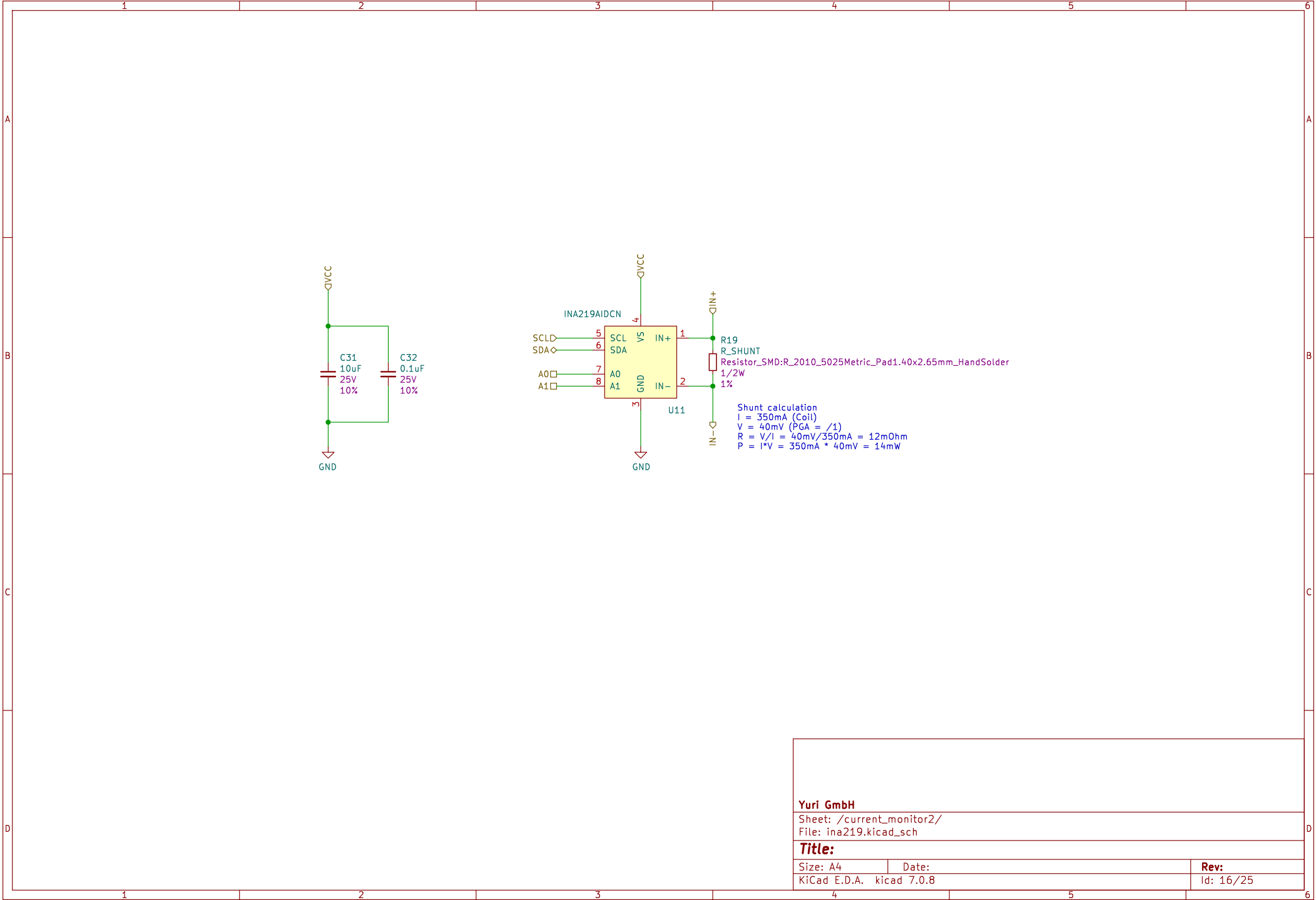
Date:

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Rev:

Id: 14/25





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Sheet: /current_monitor2/
File: ina219.kicad_sch

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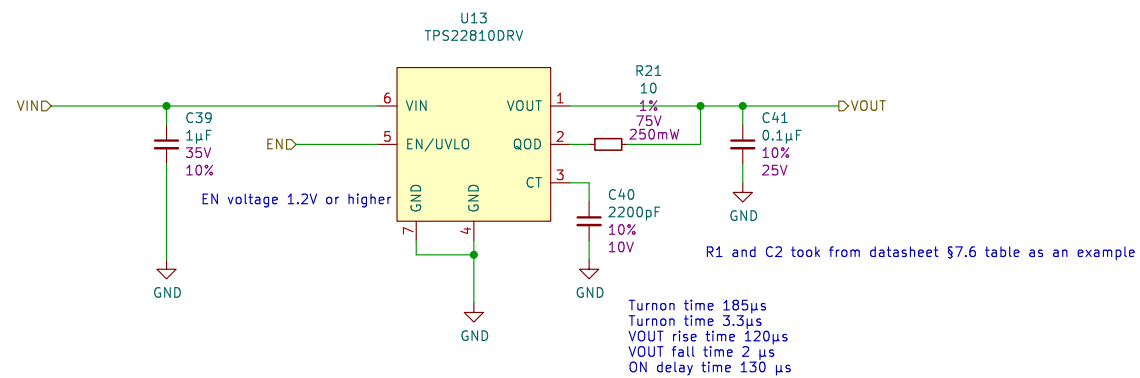
Size: A4

Date:

KiCad E.D.A. kicad 7.0.8

Rev:

Id: 16/25



R1 and C2 took from datasheet §7.6 table as an example

Turnon time 185µs
Turnon time 3.3µs
VOUT rise time 120µs
VOUT fall time 2 µs
ON delay time 130 µs

C1 = 1µF should be 10 times bigger than output capacitor.
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Sheet: /fluidic_system2/heater_switch/
File: tps22810.kicad_sch

Title:

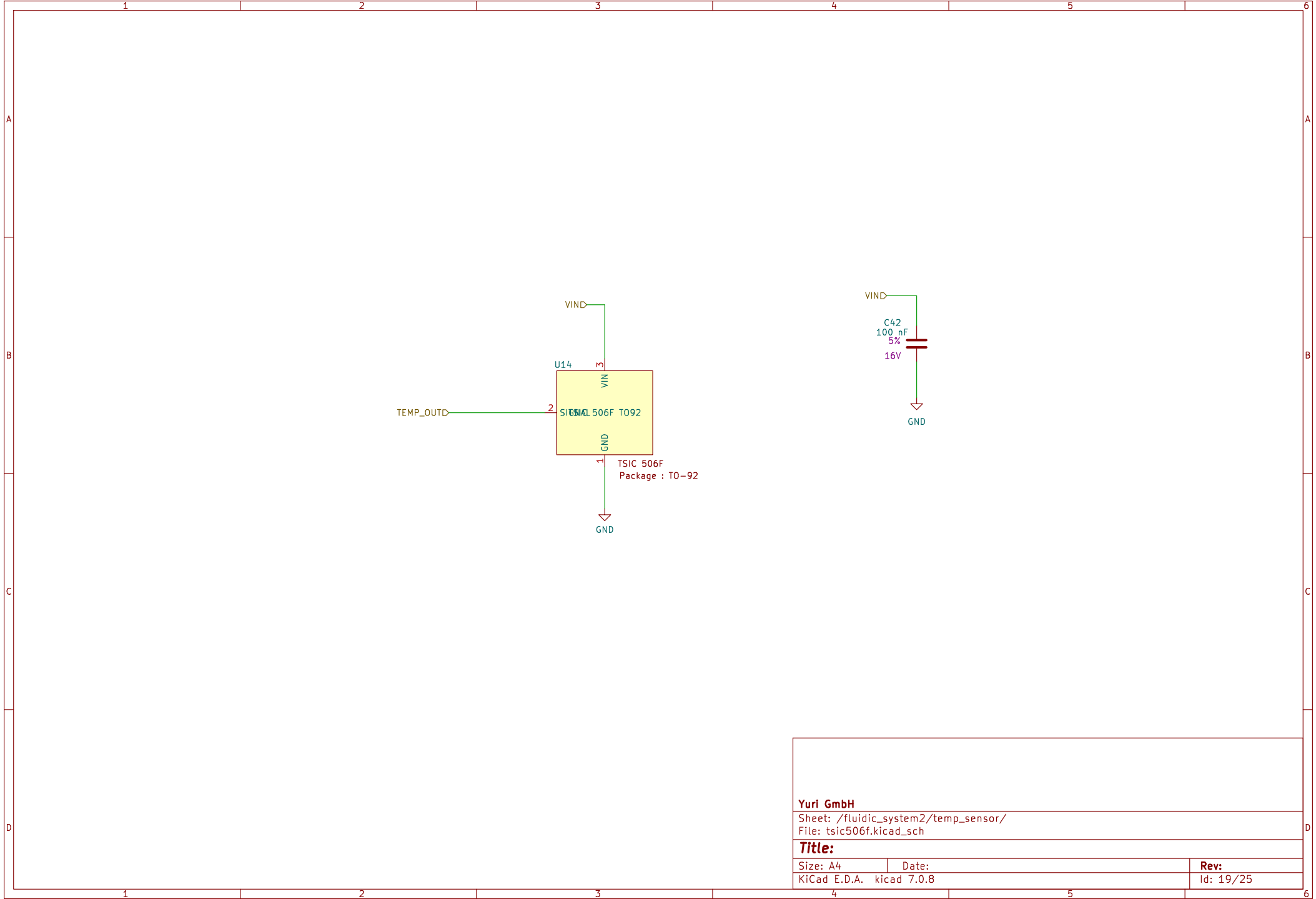
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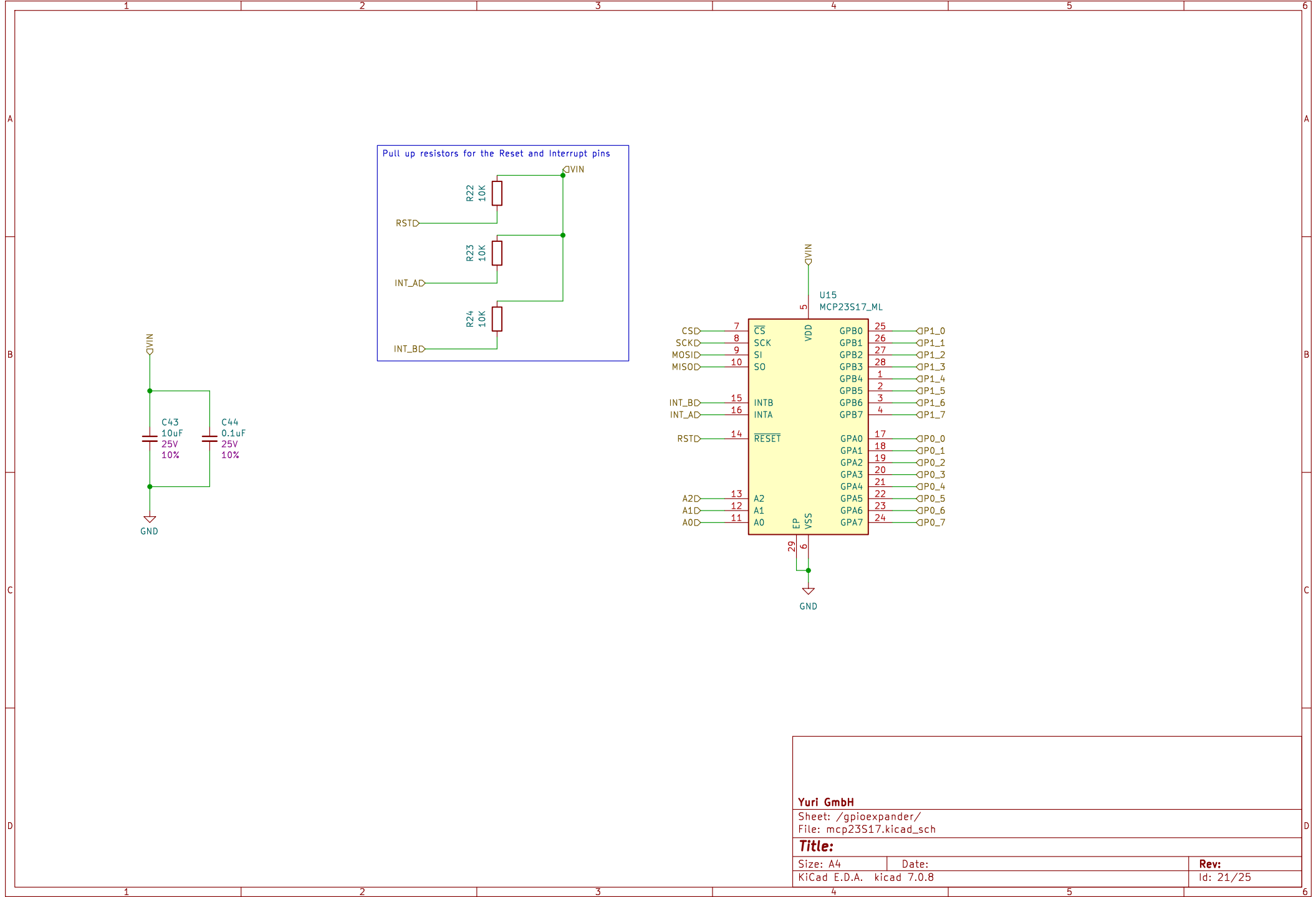
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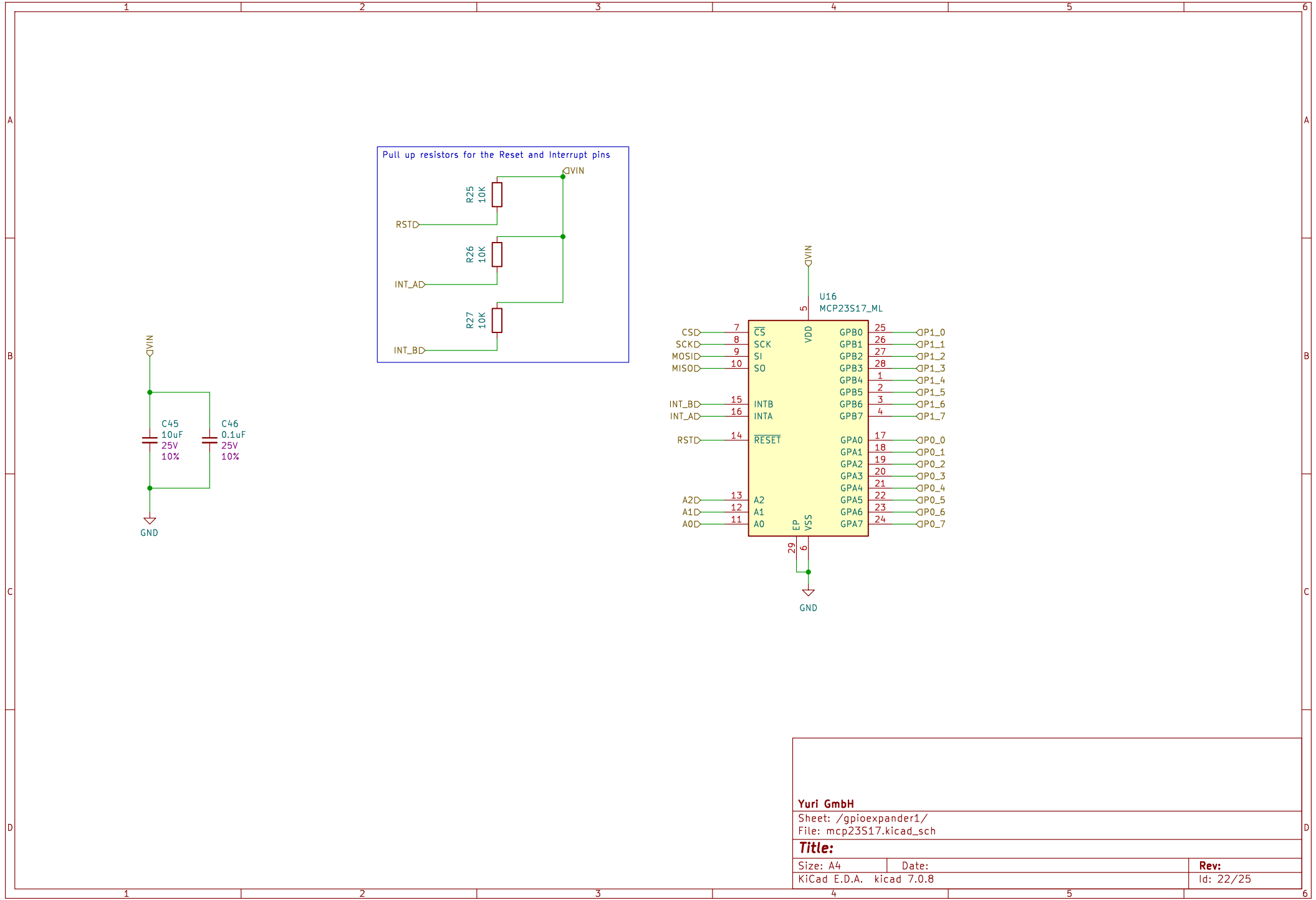
KiCad E.D.A. kicad 7.0.8

Rev:

Id: 18/25







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Sheet: /gpioexpander1/
File: mcp23S17.kicad_sch

Title:

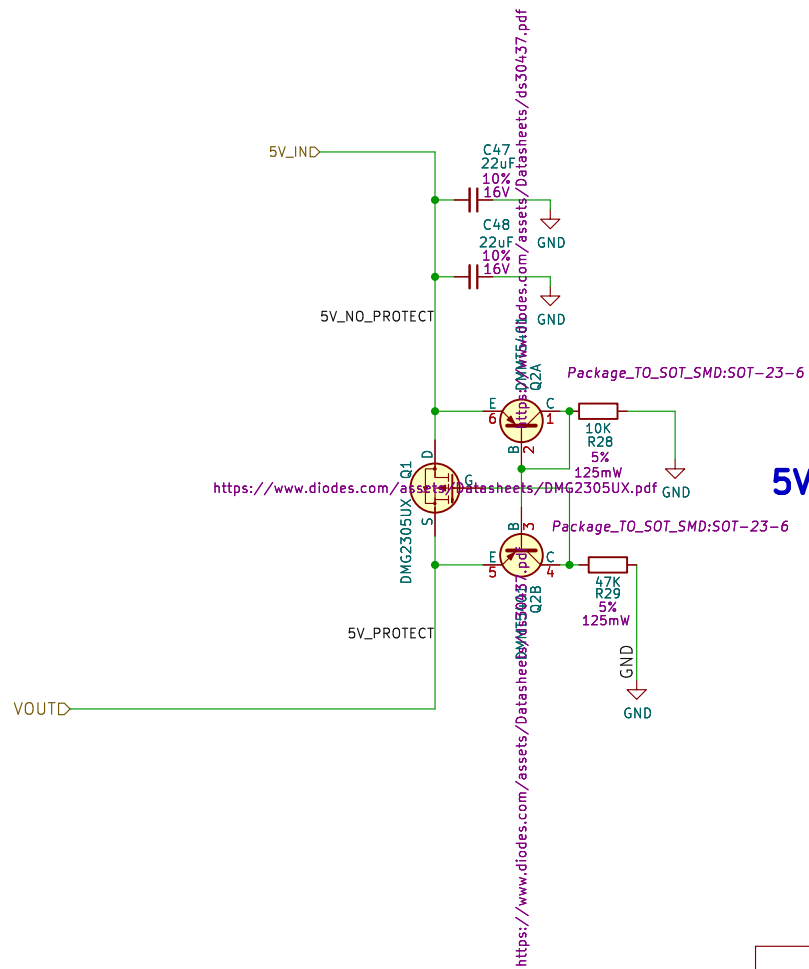
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KiCad E.D.A. kicad 7.0.8

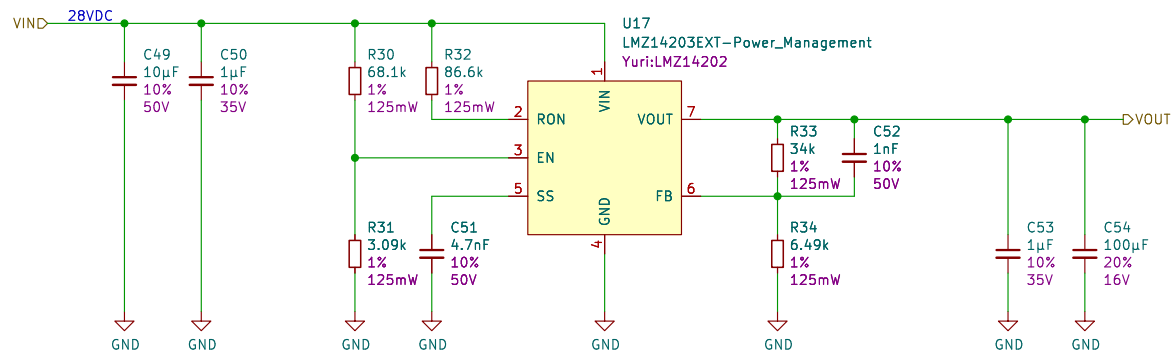
Rev:

Id: 22/25



5V Powered HAT Protection

Sheet: /5V RPi HAT Protection/ File: rpi_hat_protect.kicad_sch		
Title:		
Size: A4	Date:	Rev:
KiCad E.D.A. kicad 7.0.8	Id: 23/25	



Max input voltage is 28V from the the NyX Capsule

Output voltage 5V regulated by R4 and R5 resistors

Capacitors should be chosen with ability to handle voltage 30–50% more than voltage on the power line.

Resistors should be chosen with respect to the power.
The power dissipated by the resistors is defined by $P = U^2/R$; where U is the voltage on the power line and R is the resistance of the resistor.

Max V input at EN and FB pins is 6.5V, Use Voltage divider to bring it under this level

V_{EN} set to 1.33V through voltage divider

$V_{Out} = 0.8 V \times (1 + R_{fbt} / R_{fbb})$, where R_{fbt} is between FB and VOUT and R_{fbb} is between FB and GND

Sheet: /5V_power_supply/
File: lmz14203_5V_dc-dc.kicad_sch

Title:

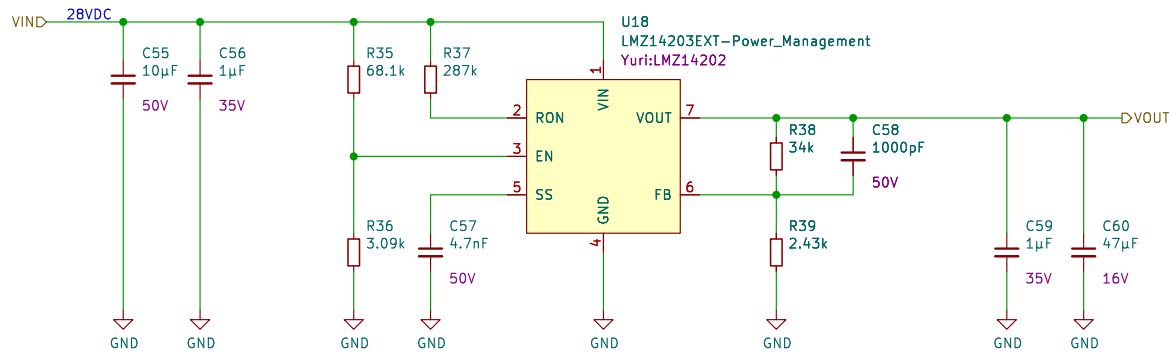
Size: A4

Date:

KiCad E.D.A. kicad 7.0.8

Rev:

Id: 23/25



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Max V input at EN and FB pins is 6.5V, Use Voltage divider to bring it under this level

V EN set to 1.33V through voltage divider

$V_{Out} = 0.8 V \times (1 + R_{fbt} / R_{fbb})$, where R_{fbt} is between FB and VOUT and R_{fbb} is between FB and GND

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Sheet: /12V_power_supply/
File: lmz14203_12V_dc-dc.kicad_sch

Title:

Size: A4

Date:

KiCad E.D.A. kicad 7.0.8

Rev:

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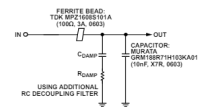
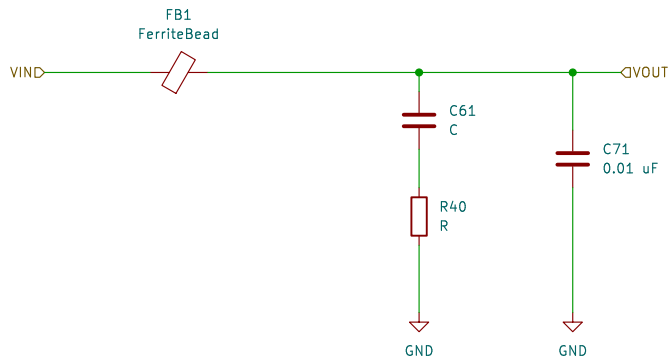


Figure 28. Additional RC Decoupling Filter

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$$R_{DAMP} \leq 0.5 \sqrt{\frac{L_{BEAD}}{C_{DECOUP}}} \quad (4)$$

where:

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$$L_{BEAD} = \frac{X_L}{2 \times \pi \times f} \quad (1)$$

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$|X_C|$ is the reactance at 803 MHz, which is 118.1 Ω.

Equation 2 yields a parasitic capacitance value (C_{DAMP}) of 1.678 pF.

Sheet: /EMI FILTER/
File: emi_filter_dc_dc.kicad_sch

Title:

Size: A5
KiCad E.D.A. kicad 7.0.8

Date:

Rev:

Id: 24/25